



HBD678

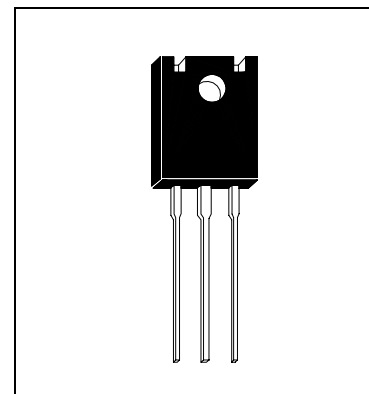
NPN EPITAXIAL PLANAR TRANSISTOR

Description

The HBD678 is designed for use as output devices in complementary general purpose amplifier applications.

Features

- High Current Gain
- Monolithic Constructor



Absolute Maximum Ratings (Ta=25°C)

- Maximum Temperatures
Storage Temperature -50 ~ +150 °C
Junction Temperature +150 °C Maximum
- Maximum Power Dissipation
Total Power Dissipation (Tc=25°C) 40 W
- Maximum Voltages and Currents
BVCBO Collector to Base Voltage 60 V
BVCEO Collector to Emitter Voltage 60 V
BVEBO Emitter to Base Voltage 5 V
IC Collector Current 4 A
IB Base Current 1 A

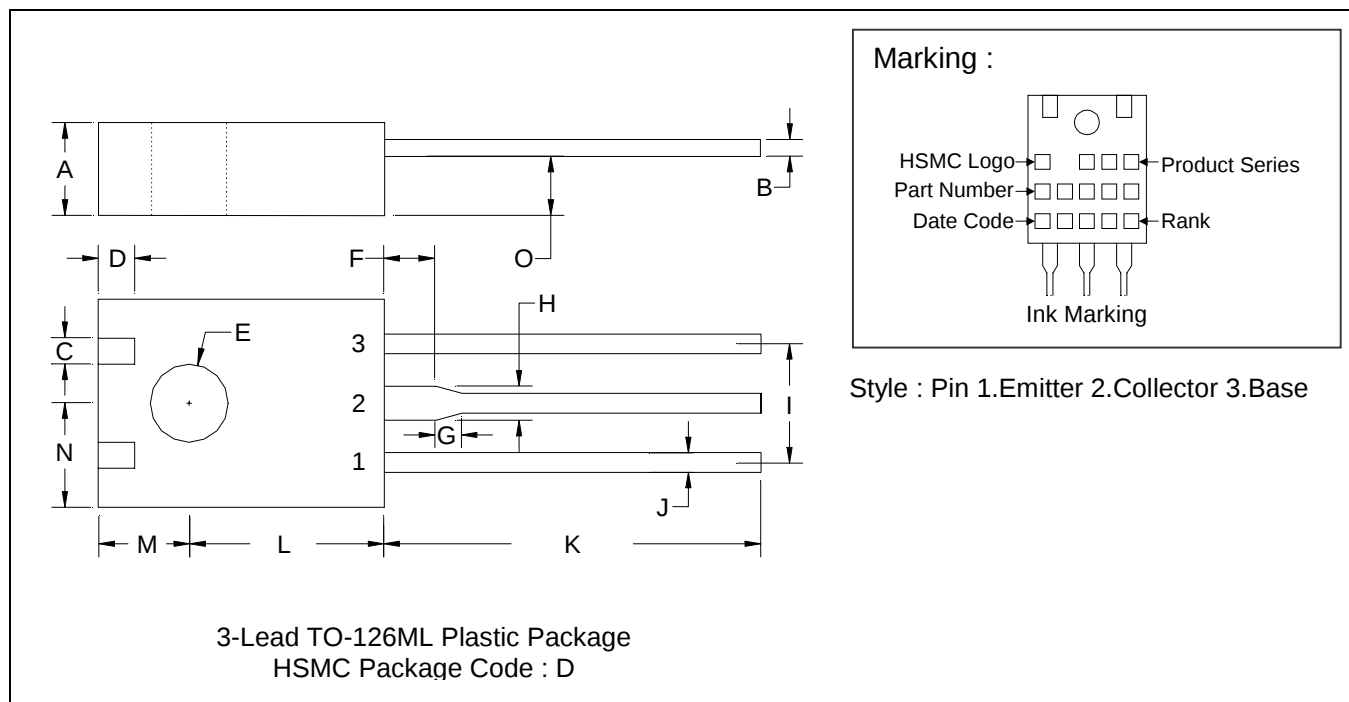
Electrical Characteristics (Ta=25°C)

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BVCBO	60	-	-	V	IC=1mA
BVCEO	60	-	-	V	IC=50mA
BVEBO	5	-	-	V	IE=1mA
ICEO	-	-	200	uA	VCB=30V
ICBO	-	-	200	uA	VCB=60V
IEBO	-	-	2	mA	VBE=5V
*VCE(sat)	-	-	2.5	V	IC=1.5A, IB=30mA
*VBE(on)	-	-	2.5	V	IC=1.5A, VCE=3V
*hFE	750	-	-		IC=1.5A, VCE=3V

*Pulse Test : Pulse Width ≤380us, Duty Cycle≤2%



TO-126ML Dimension



*:Typical

DIM	Inches		Millimeters		DIM	Inches		Millimeters	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	0.1356	0.1457	3.44	3.70	I	-	*0.1795	-	*4.56
B	0.0170	0.0272	0.43	0.69	J	0.0268	0.0331	0.68	0.84
C	0.0344	0.0444	0.87	1.12	K	0.5512	0.5906	14.00	15.00
D	0.0501	0.0601	1.27	1.52	L	0.2903	0.3003	7.37	7.62
E	0.1131	0.1231	2.87	3.12	M	0.1378	0.1478	3.50	3.75
F	0.0737	0.0837	1.87	2.12	N	0.1525	0.1625	3.87	4.12
G	0.0294	0.0494	0.74	1.25	O	0.0740	0.0842	1.88	2.14
H	0.0462	0.0562	1.17	1.42					

Notes : 1.Dimension and tolerance based on our Spec. dated Mar. 6,1995.

2.Controlling dimension : millimeters.

3.Maximum lead thickness includes lead finish thickness, and minimum lead thickness is the minimum thickness of base material.

4.If there is any question with packing specification or packing method, please contact your local HSMC sales office.

Material :

- Lead : 42 Alloy ; solder plating
- Mold Compound : Epoxy resin family, flammability solid burning class:UL94V-0

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